



DMN62D0UT

Product Summary

BV _{DSS}	R _{DS(ON)} max	I _D max T _A = +25°C	
co)/	2Ω @ V _{GS} = 4.5V	220 4	
60V	2.5Ω @ V _{GS} = 2.5V	320mA	

Description

This MOSFET is designed to minimize the on-state resistance $(R_{DS(ON)})$ and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

- Motor Control
- Power Management Functions

N-CHANNEL ENHANCEMENT MODE MOSFET

Features

- Low On-Resistance: R_{DS(ON)}
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected Up To 1kV
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

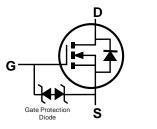
- Case: SOT523
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Alloy 42 Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Terminal Connections: See Diagram
- Weight: 0.002 grams (Approximate)



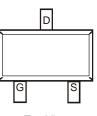


SOT523

Top View



Equivalent Circuit



Top View Pin Out

Ordering Information (Note 4)

Part Number	Case	Packaging
DMN62D0UT-7	SOT523	3,000/Tape & Reel
DMN62D0UT-13	SOT523	10,000/Tape & Reel

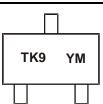
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green"

and Lead-free. 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



TK9 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: D = 2016) M = Month (ex: 9 =September)

Date Code Key

Notes:

Year	2016	2	2017	2018		2019	2020		2021	2022		2023
Code	D		E	F		G	Н		I	J		К
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings ($@T_A = +25^{\circ}C$ unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	60	V
Gate-Source Voltage	V _{GSS}	±20	V		
Continuous Drain Current (Note 6) V_{GS} = 4.5V	Steady State	T _A = +25°C T _A = +70°C	ID	320 260	mA
Maximum Continuous Body Diode Forward Curren	Is	0.4	А		
Pulsed Drain Current (10µs pulse, duty cycle = 1%	I _{DM}	1.2	А		

Thermal Characteristics (@T_A = +25°C unless otherwise specified.)

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)		PD	230	mW
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{0JA}	546	°C/W
Total Power Dissipation (Note 6)		PD	340	mW
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{θJA}	377	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)	• •					·
Drain-Source Breakdown Voltage	BV _{DSS}	60		_	V	$V_{GS} = 0V, I_D = 10\mu A$
Zero Gate Voltage Drain Current	I _{DSS}		-	1.0	μA	$V_{DS} = 60V, V_{GS} = 0V$
Gate-Source Leakage	Igss			±10	μA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	0.5	—	1.0	V	$V_{DS} = 10V, I_D = 250\mu A$
			1.2	2.0		$V_{GS} = 4.5 V, I_D = 0.1 A$
Static Drain-Source On-Resistance	R _{DS(ON)}	_	1.4	2.5	Ω	V _{GS} = 2.5V, I _D = 0.05A
			1.8	3.0		$V_{GS} = 1.8V, I_D = 0.05A$
Forward Transconductance	Y _{fs}	_	1.8	_	S	$V_{DS} = 10V, I_D = 0.2A$
Diode Forward Voltage	V _{SD}	_	0.8	1.3	V	$V_{GS} = 0V, I_{S} = 115mA$
DYNAMIC CHARACTERISTICS (Note 8)				-	-	-
Input Capacitance	Ciss	—	32	_	pF	
Output Capacitance	Coss		3.9	_	pF	V _{DS} = 30V, V _{GS} = 0V f = 1.0MHz
Reverse Transfer Capacitance	C _{rss}		2.4	_	pF	1 = 1.000112
Gate Resistance	Rg	_	101	_	Ω	$f = 1MHz$, $V_{GS} = 0V$, $V_{DS} = 0V$
Total Gate Charge	Qg	-	0.5		nC	
Gate-Source Charge	Q _{gs}		0.09	_	nC	V _{GS} = 4.5V, V _{DS} = 10V, In = 250mA
Gate-Drain Charge	Q _{gd}	-	0.09		nC	ID = 25011A
Turn-On Delay Time	t _{D(ON)}	_	2.4	_	ns	
Turn-On Rise Time	t _R	—	2.5	_	ns	$V_{DD} = 30V, V_{GS} = 10V,$
Turn-Off Delay Time	t _{D(OFF)}	_	22.6	_	ns	R _G = 25Ω, I _D = 200mA
Turn-Off Fall Time	t _F	—	12.5	_	ns	

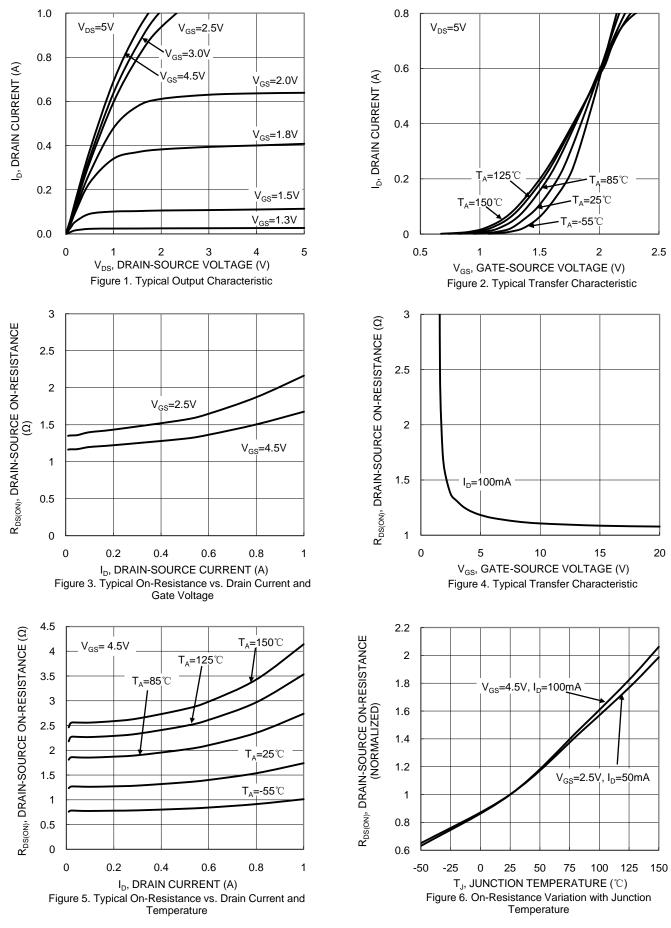
5. Device mounted on FR-4 PCB, with minimum recommended pad layout. Notes:

Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
Short duration pulse test used to minimize self-heating effect.

8. Guaranteed by design. Not subject to product testing.



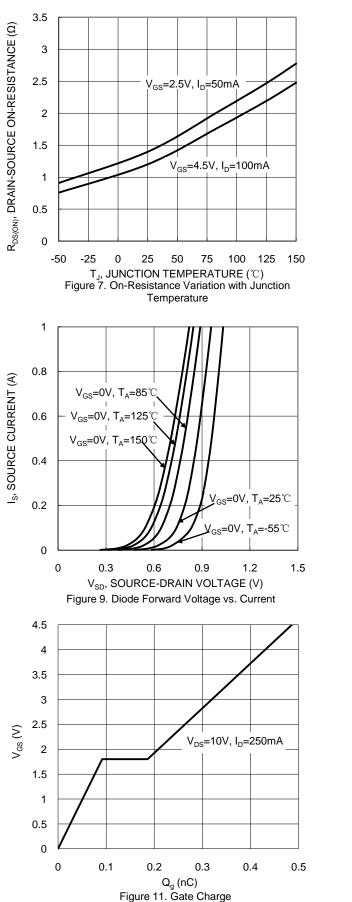
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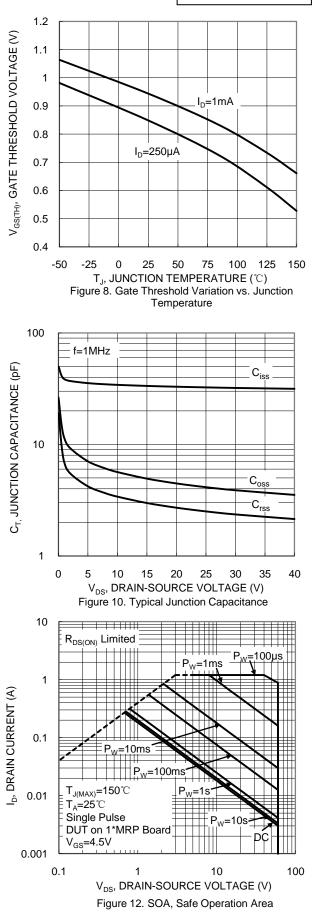


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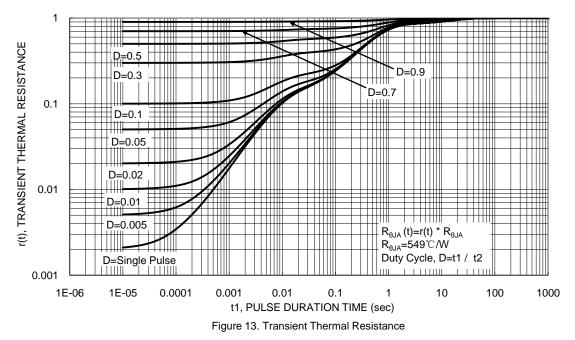










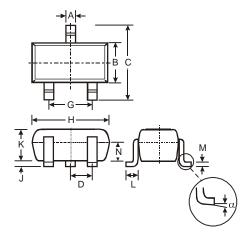




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT523

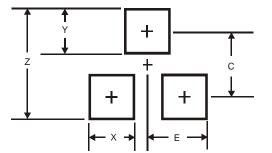


	SOT523							
Dim	Min	Max	Тур					
Α	0.15	0.30	0.22					
В	0.75	0.85	0.80					
С	1.45	1.75	1.60					
D	_		0.50					
G	0.90	1.10	1.00					
Н	1.50	1.70	1.60					
J	0.00	0.10	0.05					
Κ	0.60	0.80	0.75					
L	0.10	0.30	0.22					
М	0.10	0.20	0.12					
Ν	0.45	0.65	0.50					
α	0°	8°						
All	Dimens	ions in	mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT523



Dimensions	Value (in mm)
Z	1.8
Х	0.4
Y	0.51
С	1.3
E	0.7



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